

# Final Exam, ECE 137A

Thursday March 17, 12 - 3 p.m.

Name: \_\_\_\_\_

Closed Book Exam:

Class Crib-Sheet and 4 pages (4 surfaces) of student notes permitted

Do not open this exam until instructed to do so. Use any and all reasonable approximations (5% accuracy), *after stating & justifying them.*

**Show your work:**

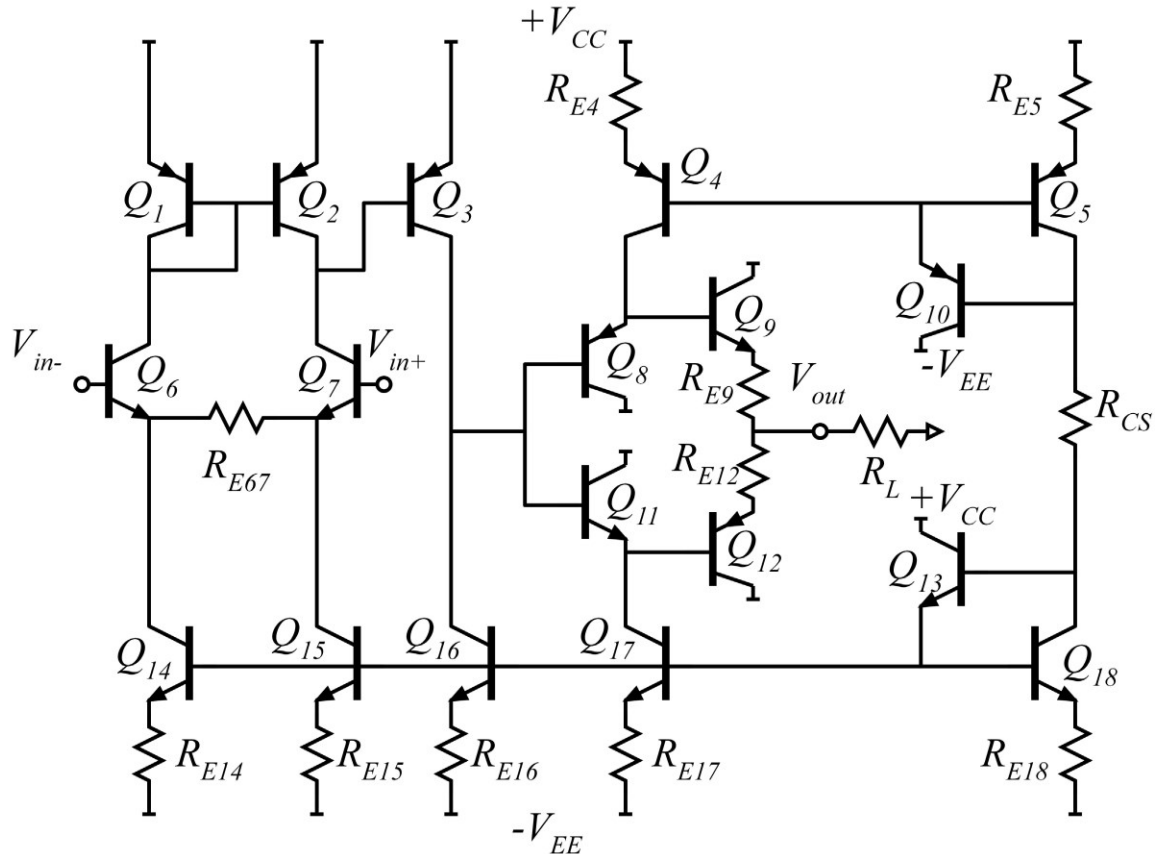
**Full credit will not be given for correct answers if supporting work is missing.**

Good luck

Part	Points Received	Points Possible	Part	Points Received	Points Possible
1a		6	2c		10
1b		5	2d		10
1c		4	3a		10
1d		10	3b		10
1e		10	3c		10
2a		10			
2b		5			
<b>total</b>		<b>100</b>			

**Problem 1, 35 points**

**This is an Op-Amp**---analyze the bias under the assumption that DC output voltage is zero volts, that the positive input  $V_{i+}$  is zero volts, and that we must determine the DC value of the negative input voltage ( $V_{i-}$ ) necessary to obtain this.



All the transistors have the same (matched)  $I_S$ , have  $\beta = 100$ , and  $V_A = \text{*infinity*}$  Volts .

$V_{CE(sat)} = 0.5V$  .  $V_{be}$  is approximately 0.7 V, but use  $V_{be} = (kT/q) \ln(I_E / I_S)$  when

necessary or appropriate. The supplies are +3 Volts and -3 Volts.

All transistors have the same  $I_S$  .

The resistors  $R_{E5}$  and  $R_{E18}$  have a 300mV DC voltage drop across them.

$R_{E67} = 100$  Ohms,  $R_L = 1000$  Ohms.

DC bias currents:  $I_{C6} = I_{C7} = I_{C9} = I_{C12} = I_{C18} = 0.1$  mA.  $I_{C3} = I_{C8} = I_{C11} = 0.2$  mA

Part a, 6 points

DC bias---to simplify ,assume  $\beta = \infty$  *for the DC analysis only.*

Analyze the bias under the assumption that DC output voltage is zero volts, that the positive input  $V_{i+}$  is zero volts, and that we must determine the DC value of the negative input voltage ( $V_{i-}$ ) necessary to obtain this.

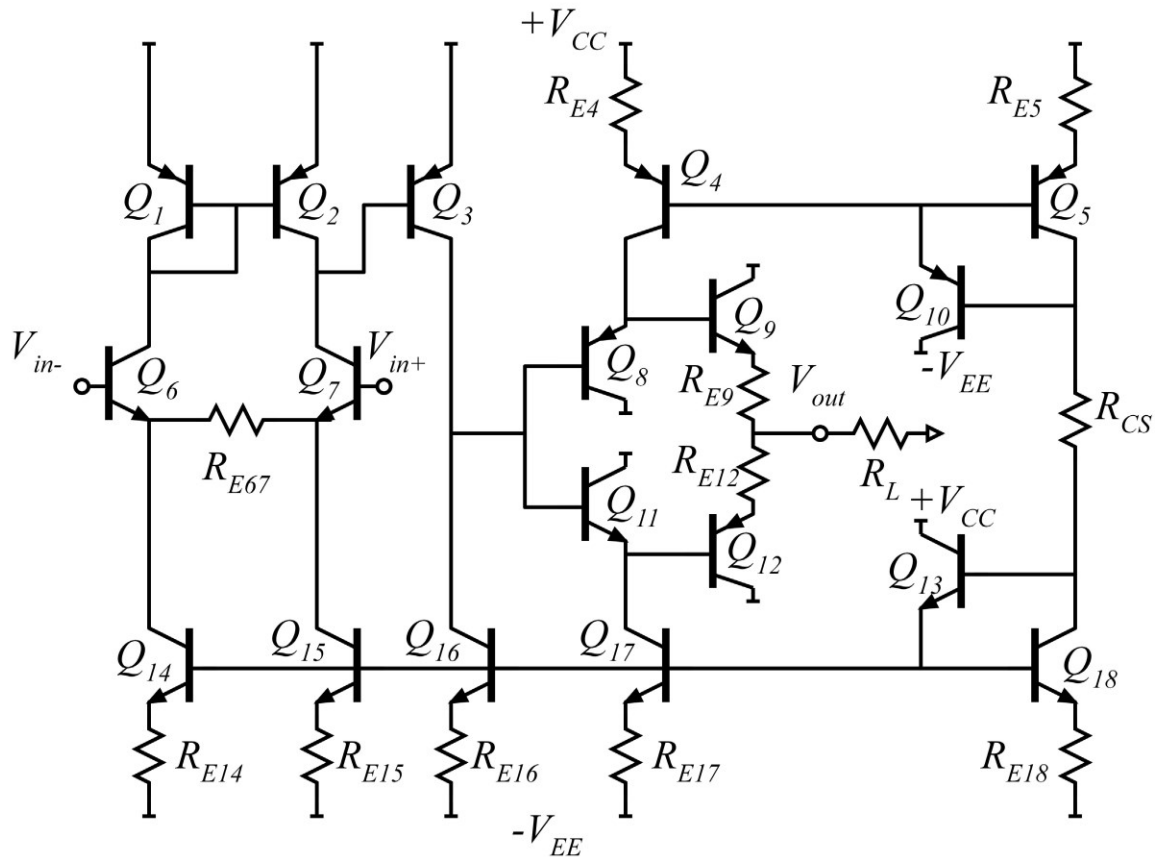
(Hint, this should give  $V_{i-} = 0V$ )

Find the value of the following resistors:

Re4= \_\_\_\_\_, Re5= \_\_\_\_\_, Re9= \_\_\_\_\_, Re12= \_\_\_\_\_, Re14= \_\_\_\_\_,  
Re15= \_\_\_\_\_, Re16= \_\_\_\_\_, Re17= \_\_\_\_\_, Re18= \_\_\_\_\_, Rcs= \_\_\_\_\_,



Part b, 5 points



On the circuit diagram above, label the DC voltages at **ALL nodes**, and the DC collector currents of **all transistors**. Label the values of all resistors.



Part c, 4 points

find the following

device	Q1	Q2	Q3	Q4	Q5	Q6	Q7	Q8
gm, mS								

device	Q9	Q10	Q11	Q12	Q13	Q14	Q15	Q16
gm, mS		don't bother*			don't bother*			

device	Q17	Q18
gm, mS		

\*don't bother calculating these





Part d, 10 points.

Find the following, *using the actual value of  $\beta$ , i.e.  $\beta=100$*

	Voltage Gain	Input impedance
Q9 or Q12		
Q8 or Q11		
Q3		
Q1,2,6,7 combination.		
Overall differential $V_{out}/V_{in}$		







Part e, 10 points

Maximum peak-peak output voltage (*show all your work*)

For this, you must use the full circuit diagram, not the half circuit diagram.

	magnitude and sign of maximum output signal swing due to <i>cutoff</i>	magnitude and sign of maximum output signal swing due to <i>saturation</i>
Transistor Q9		
Transistor Q12		
Transistor Q8		
Transistor Q11		
Transistor Q4		
Transistor Q17		

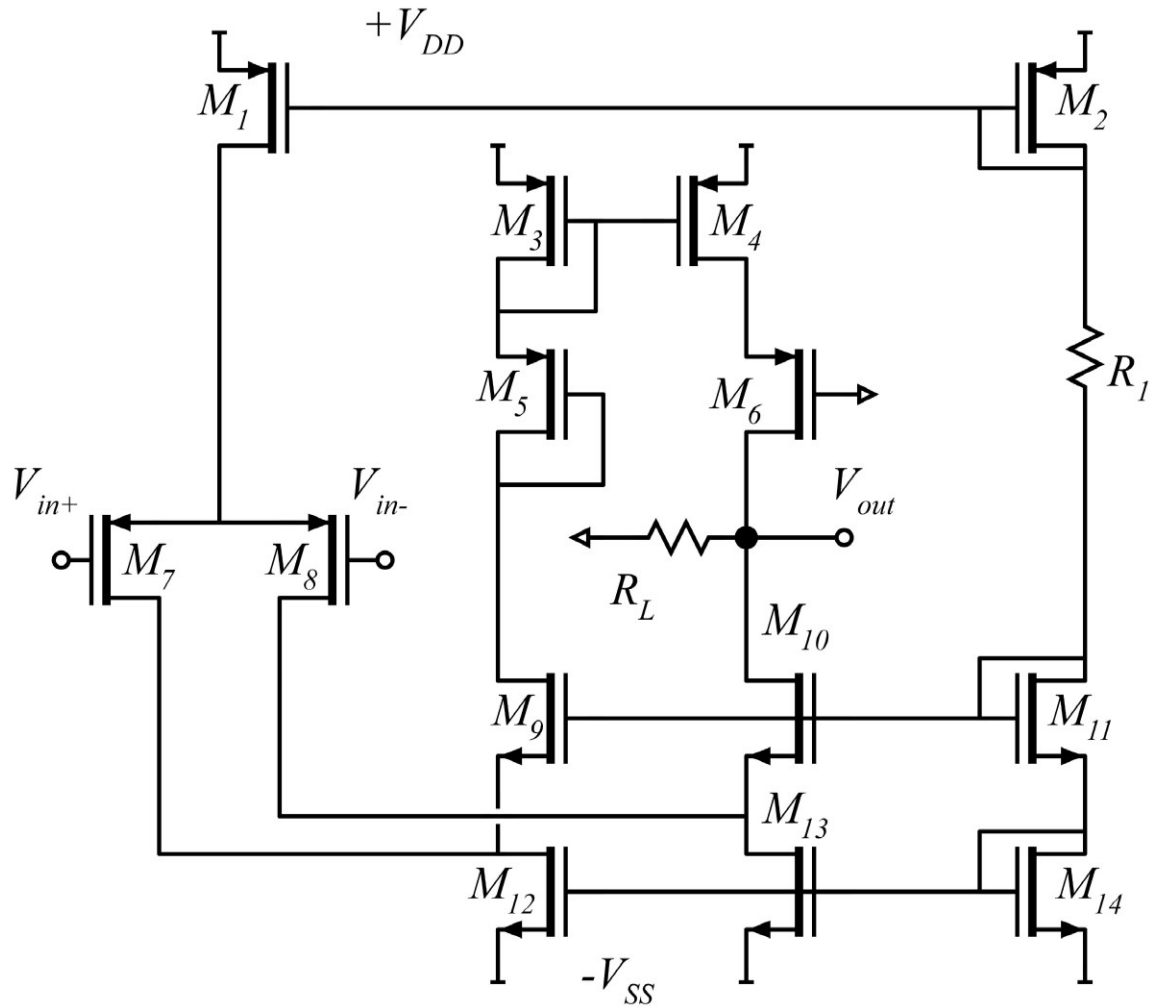
Be warned: In some cases a limit is not relevant at all. Mark those answers "not relevant". But, give a 1-sentence statement below as to why it is not relevant. Q9/12 form a push pull stage, so be careful about your answer there. .





**Problem 2, 35 points**

**This is an NOT an Op-Amp:** Analyze under the assumption that the differential and common mode input voltages are at zero volts



The NMOSFETs have  $K_{\mu} = \mu c_{gs} W_g / 2L_g = 10\text{mA/V}^2 \cdot (W_g / 1\mu\text{m})$

$K_v = c_{gs} v_{inj} W_g = 2.0\text{mA/V} \cdot (W_g / 1\mu\text{m})$ ,  $\Delta V = v_{inj} L_g / \mu = 0.10\text{V}$ ,  $V_{th} = 0.3\text{V}$ ,

$1/\lambda = 5\text{V}$

The PMOS have identical parameters, except, of course,  $V_{th}$  is negative.

$V_{DD} = +0.8\text{V}$ ,  $-V_{SS} = -0.8\text{V}$ ,  $R_L = 10\text{k}\Omega$

All transistors have  $|V_{gs}| = 0.4\text{V}$

M7,8 are biased at  $I_D = 50\mu\text{A}$ .

M5,6,9,10,11 are biased at  $I_D = 200\mu\text{A}$



Part a, 10 points

DC bias.

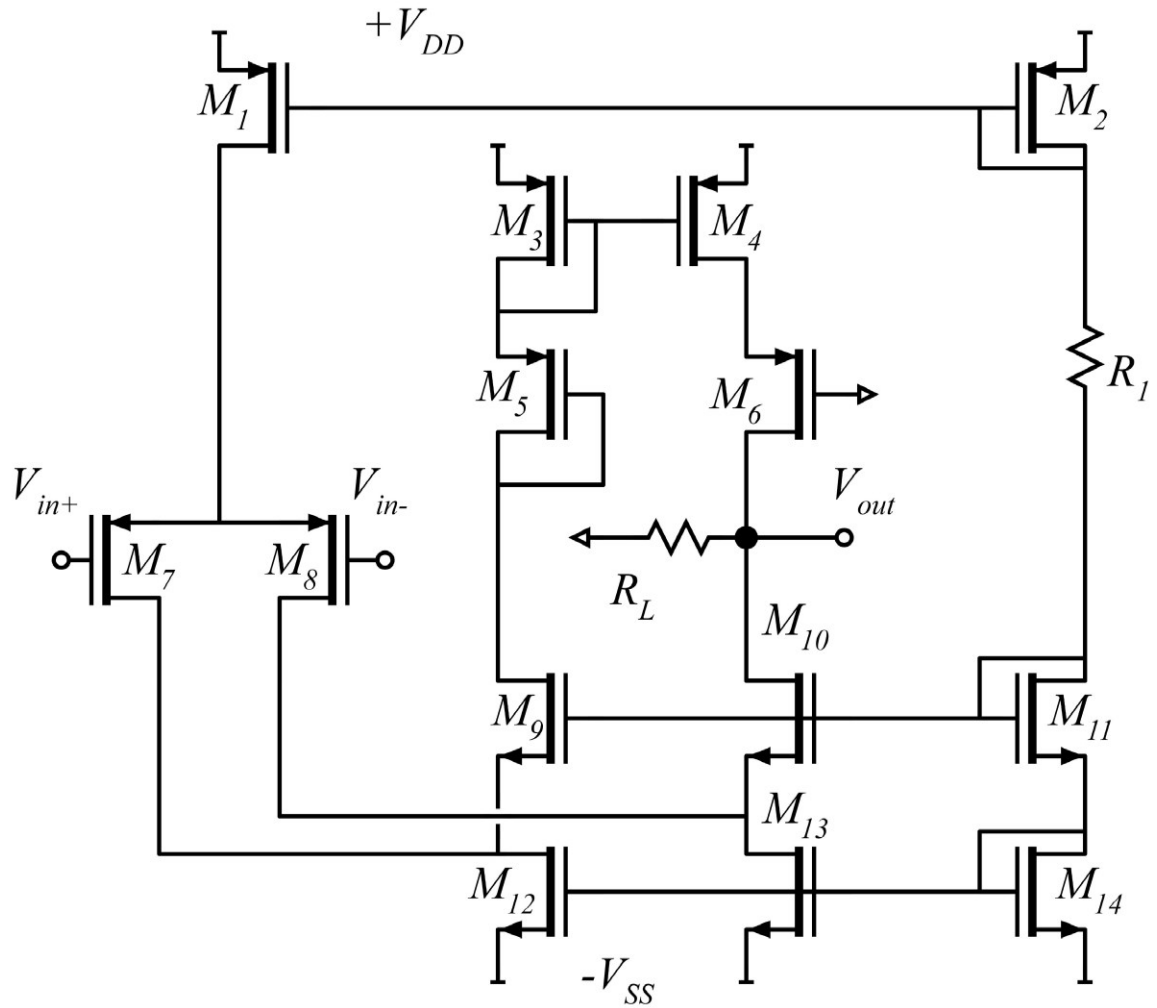
Find the Gate widths, in  $\mu\text{m}$ , of  
M1 \_\_\_\_\_, M7 \_\_\_\_\_

Note that, by using the mobility-limited formula  $g_m = 2I_D / (V_{gs} - V_{th})$ , we can solve the exam without calculating any of the FET widths. ***So, there's no reason to spend time calculating other FET widths.***



Part b, 5 points

DC bias



On the circuit diagram above, label the DC voltages at **ALL nodes**, the drain currents of **ALL transistors**



Part c, 10 points.

This amplifier has *two* signal paths between input and output.

One is the path (M7 and M8, M9, M3, M4, M6, output).

The other is the path (M7 and M8, M10, output).

***You will now compute the differential gain for the path (M7 and M8, M10, output).***

Find the following

	Voltage Gain	Input impedance
Transistor M10		
M7-M8 differential pair		
Overall differential $V_{out}/V_{in}$ for this path		











Part d, 10 points

This amplifier has *two* signal paths between input and output.

One is the path (M7 and M8, M9, M3, M4, M6, output).

The other is the path (M7 and M8, M10, output).

***You will now compute the differential gain for the path (M7 and M8, M9, M3, M4, M6, output).*** Find the following

	Voltage Gain	Input impedance
Transistor M6		
Transistor M4		
Transistor M9		
M7-M8 differential pair		
Overall differential Vout/Vin for this path		

(the overall amplifier gain is the sum of the answers for parts c and d, but you are not asked to calculate this.)





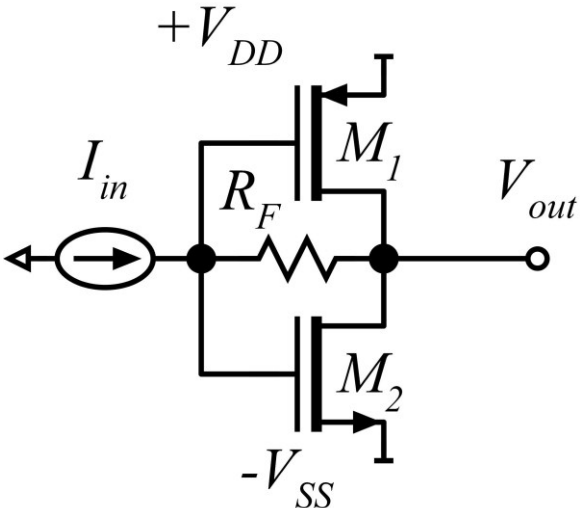




**Problem 3, 30 points**

*Nodal analysis: optical receiver preamplifier as real-world example.*

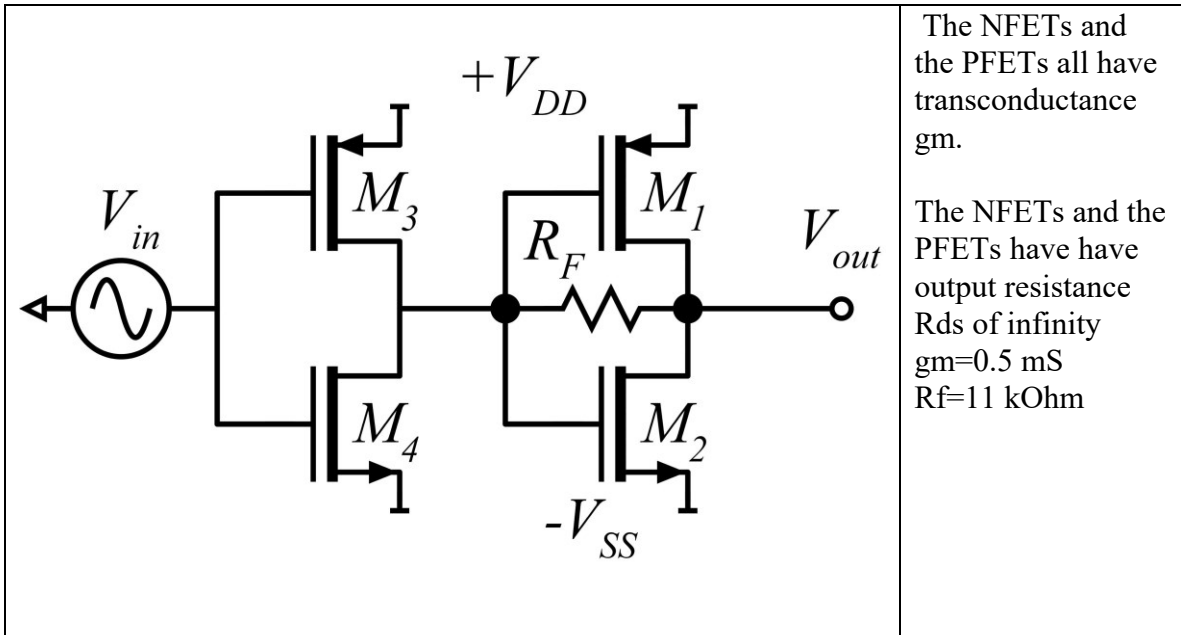
Part a, 10 points

	<p>You will be working on the circuit to the left</p> <p>Ignore DC bias analysis. You don't need it.</p> <p>The NFET and the PFET each have transconductance <math>g_m</math>.</p> <p>The NFET and the PFET each have output resistance <math>R_{ds}</math> of infinity...so you don't need to include this element in the circuit diagram !</p> <p><math>g_m=0.5 \text{ mS}</math> <math>R_f=11 \text{ k}\Omega</math></p>
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Compute, from nodal analysis, the small-signal gain  $V_{out}/I_{in}$ . This is called a transimpedance gain.

$V_{out}/I_{in} =$  \_\_\_\_\_

Part b, 10 points



The NFETs and the PFETs all have transconductance  $g_m$ .

The NFETs and the PFETs have have output resistance  $R_{ds}$  of infinity  
 $g_m = 0.5 \text{ mS}$   
 $R_f = 11 \text{ k}\Omega$

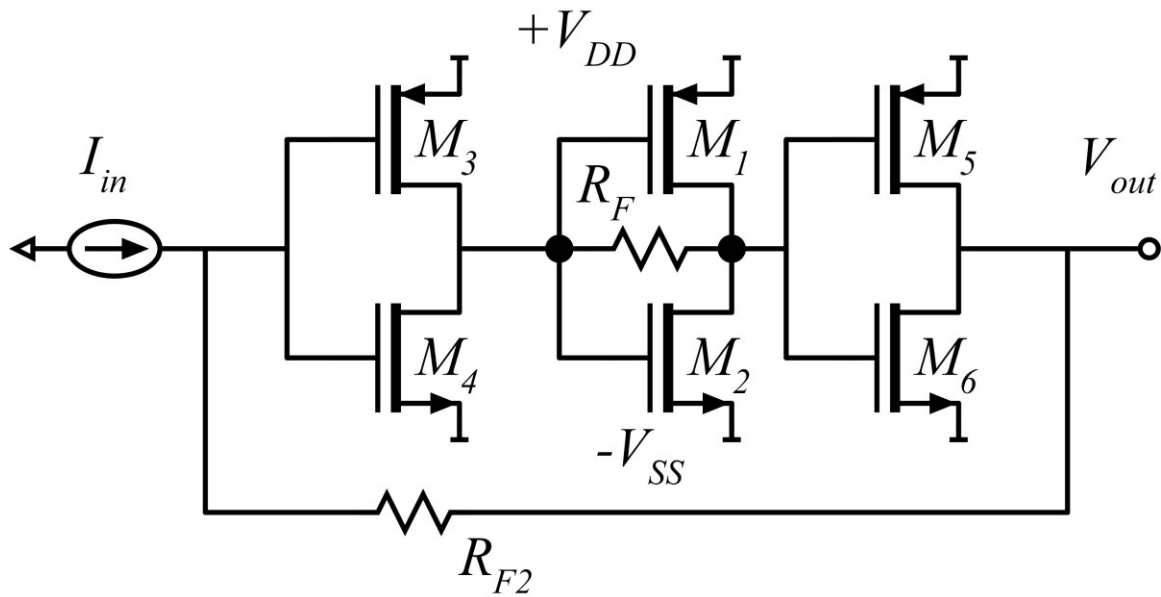
Compute, from nodal analysis, the small-signal gain  $V_{out}/V_{in}$ . This is a voltage gain.  
 Hint: you can save some work by using the result from part A.

$V_{out}/V_{in} =$  \_\_\_\_\_





Part c, 10 points



The NFETs and the PFETs all have transconductance  $g_m$ . The NFETs and the PFETs have have output resistance  $R_{ds}$  of infinity.  
 $g_m=0.5 \text{ mS}$ ,  $R_f=11 \text{ k}\Omega$ ,  $R_{f2}=1 \text{ k}\Omega$ .

Compute, from nodal analysis, the small-signal gain  $V_{out}/I_{in}$ . This is a transimpedance gain. Hint: you can save a great deal of work by using the results from parts A and B.

$V_{out}/I_{in} = \underline{\hspace{2cm}}$